[ABSTRACT]

A method of manufacturing a mask blank according to the invention manufactures a mask blank in which a mask layer containing silicon is stacked on a transparent substrate. In the method, the mask layer is formed by sputtering using a target containing a dopant reducing a specific resistance.~~The purpose of the present invention is to solve problems of accuracy deterioration in the shape of a formed pattern which is caused by an increase in pattern thickness resulting from increase in thickness of an oxide layer formed on a surface layer of a mask layer including molybdenum when a laser is applied thereonto in an exposure step, and occurrence of a case where a mask layer of desired film characteristics cannot be obtained if a sputter target of high specific resistance is used, and to further increase the etching speed of the mask layer in a pattern forming step. A mask blank manufacturing method according to the present invention involves forming a mask layer containing silicon on a transparent substrate through sputtering using a target that includes a dopant for reducing specific resistance (S12).~~